

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-7. (Cancelled).

8. (Currently Amended) An apparatus for manufacturing a semiconductor device having a thin film on a substrate, comprising:

a washing section for washing the substrate with a washing liquid;
a liquid-removing section for removing the washing liquid from the substrate by blowing pre-heated compressed air to the substrate washed; and
a film-forming section for forming a thin film on the substrate from which the washing liquid has been removed,

wherein the liquid-removing section has an air knife which is inclined in a first direction that is horizontally perpendicular to a transfer direction of the substrate and inclined in a second direction that is vertically perpendicular to the transfer direction of the substrate so as to blow compressed air towards a rear edge of the substrate.

9. (Original) The apparatus according to claim 8, wherein the washing section comprises a brush washing section, a rinse section, and an ultrasonic washing section, in which the substrate is washed.

10. (Cancelled).

11. (Currently Amended) The apparatus according to claim 8-10, further comprising a heater for heating compressed air to be supplied to the air knife.

12. (Currently Amended) The apparatus according to claim 8 10, further comprising an ionizing section for ionizing the compressed air to be supplied to the air knife.

13. (Original) The apparatus according to claim 8, wherein the liquid-removing section has at least two air knives located above and below substrate to be transferred, inclined to the direction perpendicular to the substrate transfer direction and arranged such that the closest ends of adjacent air knives are spaced apart at a predetermined interval in the substrate transfer direction and overlap for a predetermined distance in the direction perpendicular to the substrate transfer direction.

14. (Original) The apparatus according to claim 8, wherein the film forming section comprises a film forming chamber for forming a film on the substrate and a load-lock chamber for heating the substrate to a predetermined temperature before the film is formed in the film forming chamber.

15. (Original) The apparatus according to claim 8, wherein a first supply pipe for supplying a material gas for forming a film and a second supply pipe for supplying an inert gas which is ionized, into a plasma before the film is formed, are connected to the film forming chamber.